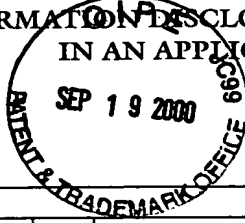
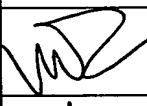
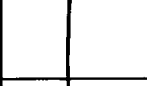

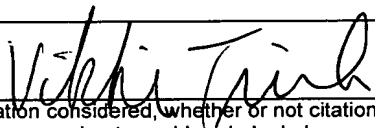


INFORMATION DISCLOSURE CITATION IN AN APPLICATION 				Docket Number		Application Number	
				M4065.0210/P210		09/588,008	
				Applicant(s)			
				Dan Gealy et al.			
				Filing Date		Group Art Unit	
				June 6, 2000		2814	
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
	REF	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translations YES NO
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
	A	G. W. Dietz et al, "LEAKAGE CURRENTS IN Ba _{0.7} Sr _{0.3} TiO ₃ THIN FILMS FOR ULTRAHIGH-DENSITY DYNAMIC RANDOM ACCESS MEMORIES," J. Appl. Phys. 82 (5), September 1, 1997, American Institute of Physics, pages 2359-2364.					
	B	Tomonori Aoyama et al., "ULTRATHIN Ta ₂ O ₅ FILM CAPACITOR WITH Ru BOTTOM ELECTRODE," J. Electrochem. Soc. Vol. 145, No. 8, August 1998, The Electrochemical Society, Inc., pages 2961-2963.					
	C	Benjamin Chih-ming Lai et al., "LEAKAGE CURRENT MECHANISM OF METAL-Ta ₂ O ₅ METAL CAPACITORS FOR MEMORY DEVICE APPLICATION," Journal of the Electrical Society, 146 (1) pages 266-269 (1999).					
EXAMINER				DATE CONSIDERED			
Not Yet Assigned							
				12/30/01			
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							

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